

Features

- $V_{DS} = 60V, I_D = 25A$
 $R_{DS(ON)} < 33m\Omega @ V_{GS} = 10V$

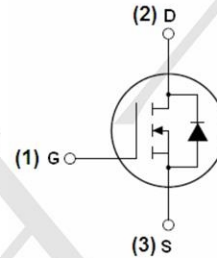
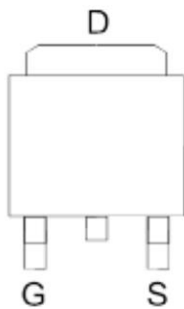
Application

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

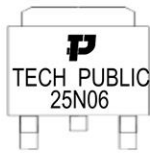
Package and Pin Configuration

(TO-252-3L)

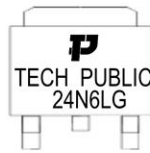
Top View



Marking:



Or



Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	25	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	20	A
Pulsed Drain Current	I_{DM}	74	A
Maximum Power Dissipation	P_D	50	W
Derating factor		0.33	W/ $^\circ C$
Single pulse avalanche energy ^(Note 5)	E_{AS}	144	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	3	$^\circ C/W$
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.4	1.8	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	26	33	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =20A	-	30	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V, F=1.0MHz	-	1900	-	PF
Output Capacitance	C _{oss}		-	130	-	PF
Reverse Transfer Capacitance	C _{rss}		-	95	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DS} =30V, R _L =1.5Ω V _{GS} =10V, R _G =3Ω	-	5	-	nS
Turn-on Rise Time	t _r		-	2.6	-	nS
Turn-Off Delay Time	t _{d(off)}		-	16.1	-	nS
Turn-Off Fall Time	t _f		-	2.3	-	nS
Total Gate Charge	Q _g	V _{DS} =30V, I _D =20A, V _{GS} =10V	-	30	-	nC
Gate-Source Charge	Q _{gs}		-	4.5	-	nC
Gate-Drain Charge	Q _{gd}		-	7.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =30A	-	-	1.2	V
Diode Forward Current	I _S		-	-	25	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =20A di/dt = 100A/μs (Note3)	-	35	-	nS
Reverse Recovery Charge	Q _{rr}		-	53	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Typical Characteristics

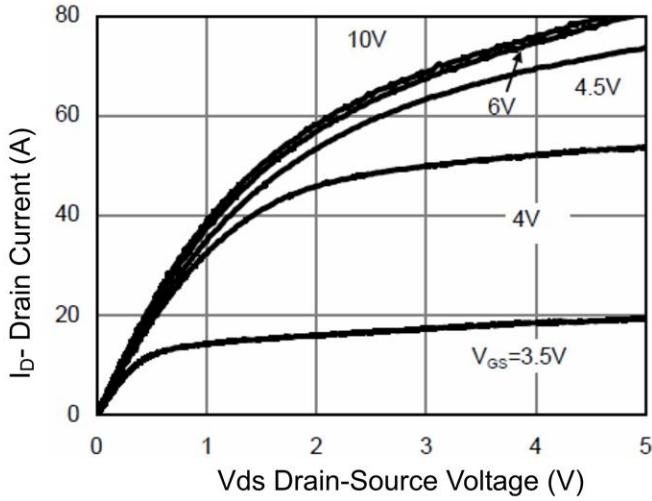


Figure 1 Output Characteristics

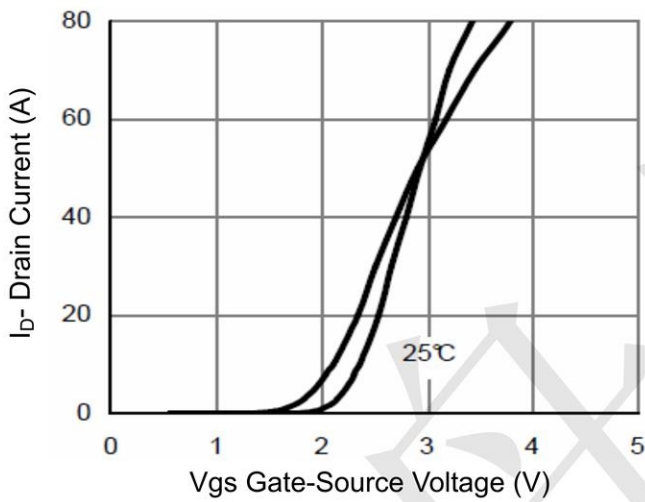


Figure 2 Transfer Characteristics

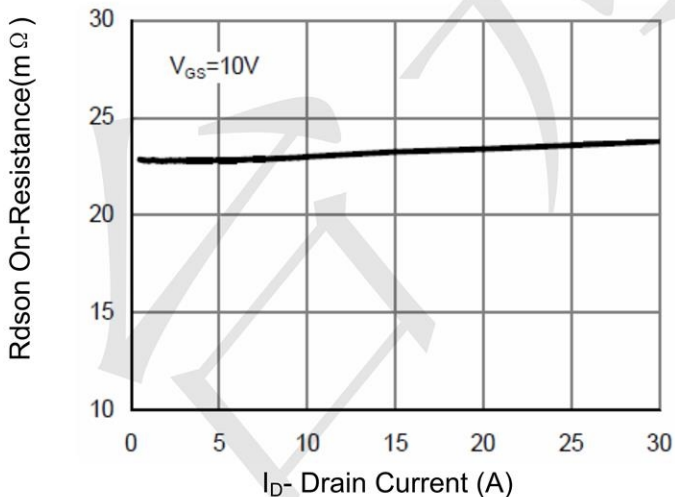


Figure 3 Rds(on)- Drain Current

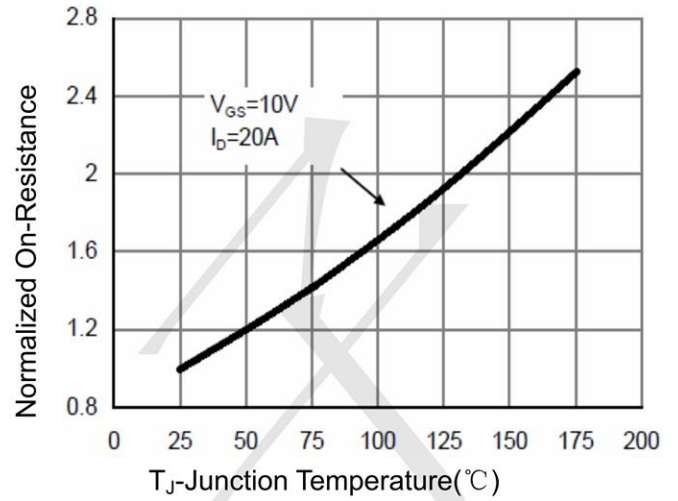


Figure 4 Rds(on)-Junction Temperature

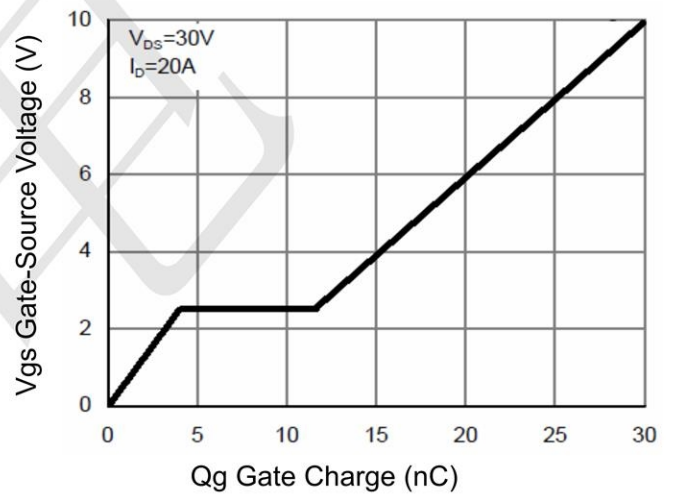


Figure 5 Gate Charge

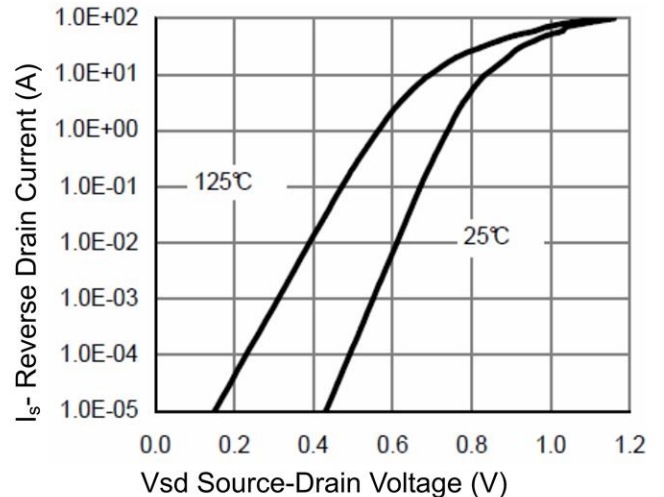


Figure 6 Source- Drain Diode Forward

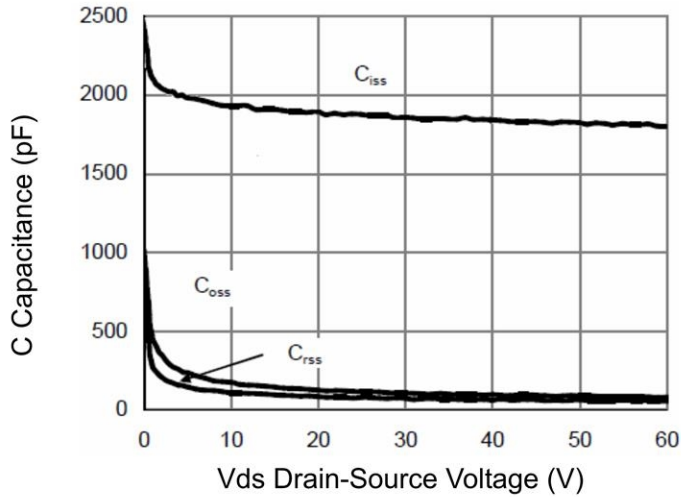


Figure 7 Capacitance vs Vds

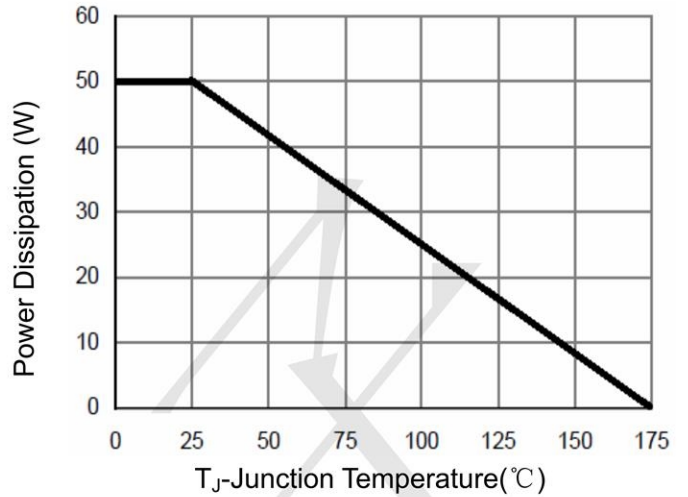


Figure 9 Power De-rating

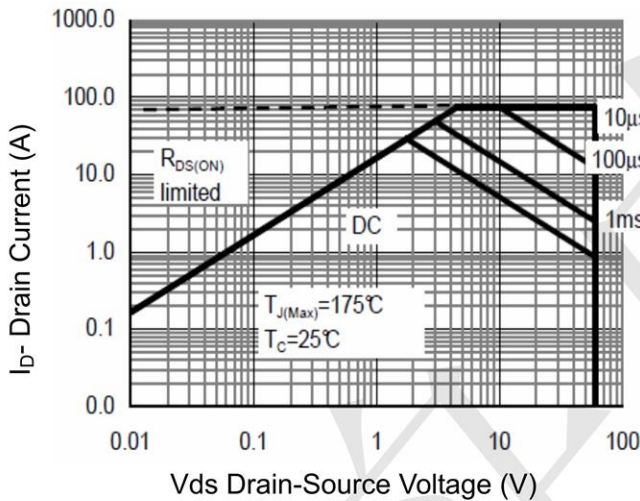


Figure 8 Safe Operation Area

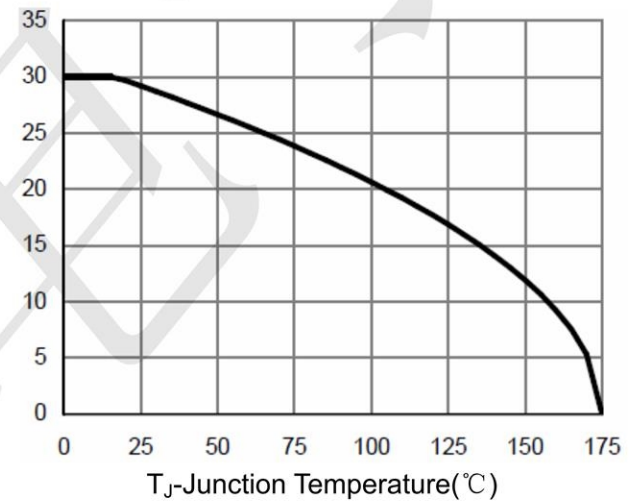


Figure 10 $V_{GS(th)}$ vs Junction Temperature

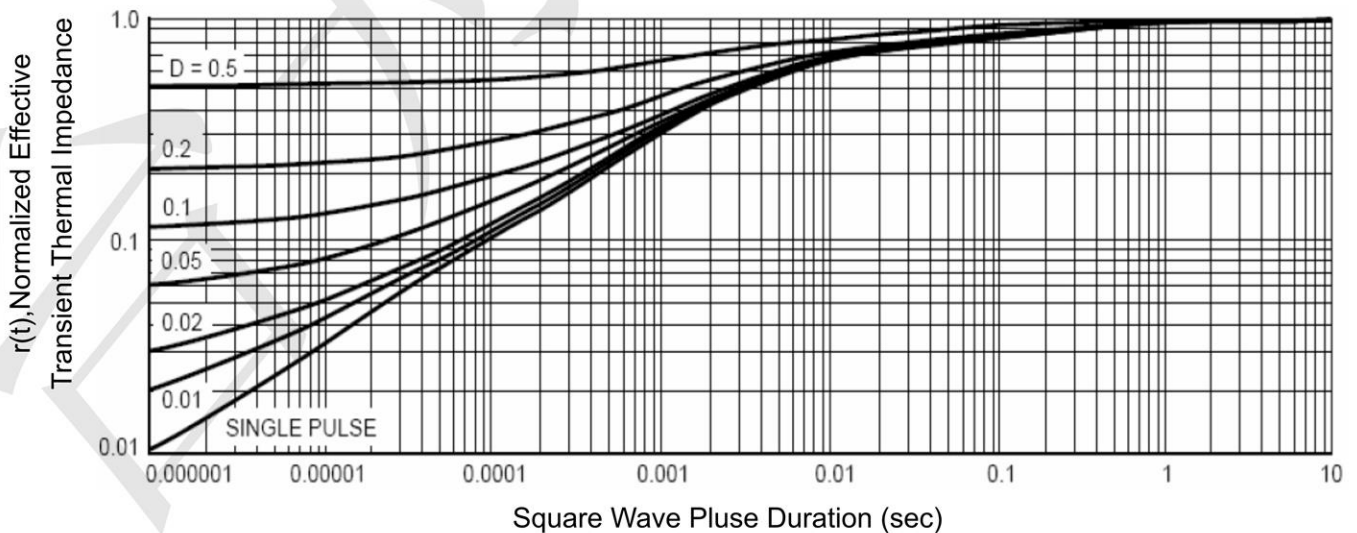
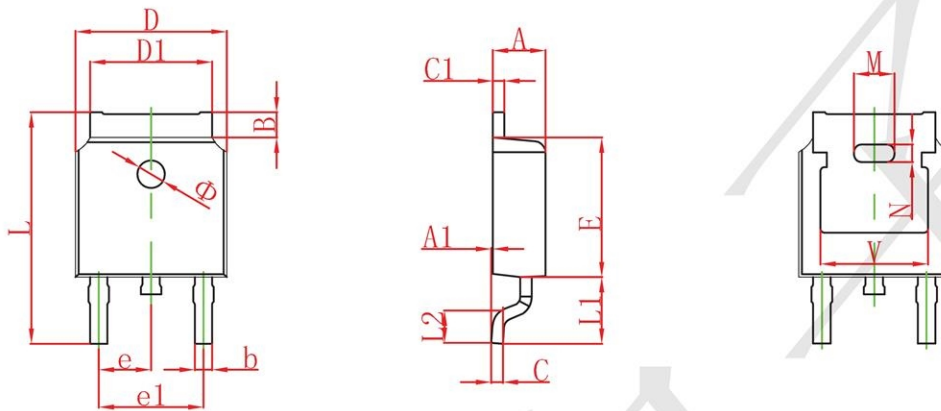


Figure 11 Normalized Maximum Transient Thermal Impedance

TO252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.380	0.087	0.094
A1	0.000	0.100	0.000	0.004
B	0.800	1.400	0.031	0.055
b	0.710	0.810	0.028	0.032
c	0.460	0.560	0.018	0.022
c1	0.460	0.560	0.018	0.022
D	6.500	6.700	0.256	0.264
D1	5.130	5.460	0.202	0.215
E	6.000	6.200	0.236	0.244
e	2.286 TYP.		0.090 TYP.	
e1	4.327	4.727	0.170	0.186
M	1.778REF.		0.070REF.	
N	0.762REF.		0.018REF.	
L	9.800	10.400	0.386	0.409
L1	2.9REF.		0.114REF.	
L2	1.400	1.700	0.055	0.067
V	4.830 REF.		0.190 REF.	
Φ	1.100	1.300	0.043	0.051